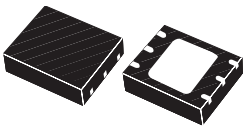
ST1S15

500 mA, 6 MHz synchronous step-down converter

Datasheet - production data

Flip Chip 6



DFN6 (2 x 2 mm)

Features

- 85% typical efficiency
- 500 mA output current capability
- 45 µA typical quiescent current
- PFM or PWM operation for best efficiency over whole load range
- Ultra-fast load and line transient
- Short-circuit and thermal protection
- Tiny external components
- Auto or forced PWM selection with dedicated pin
- Available in Flip Chip 6 and DFN6 (2 x 2 mm) packages

Applications

- DSP and multimedia processors core supply
- Cell phones
- PDAs

Description

The ST1S15 is a high efficiency miniaturized step-down converter able to provide 500 mA output current from an input voltage from 2.3 V to 5.5 V. This converter is specifically designed for applications where high efficiency and small a application area are the key factors. With an output voltage as low as 0.6 V the device supports low voltage DSPs and processors core supply. Due to the 6 MHz switching frequency the ST1S15 can use nominal values of 470 nH for the inductor and 4.7 µF for the output capacitor, providing, at the same time, very good performance in terms of load and line transients. It is possible to select a PFM mode for high efficiency under light load conditions or PWM mode for tight regulation and best dynamic performance. Short-circuit and thermal protection are also included.

Table 1. Device summary

Order codes	Output voltages (V)	Packages
ST1S15J18R	1.82	Flip Chip 6
ST1S15J28R	2.8	
ST1S15TPUR	1.82	DFN6 (2 x 2 mm)
ST1S15-28TPUR	2.8	

Contents

1 Application schematic

Figure 1. ST1S15 application schematic

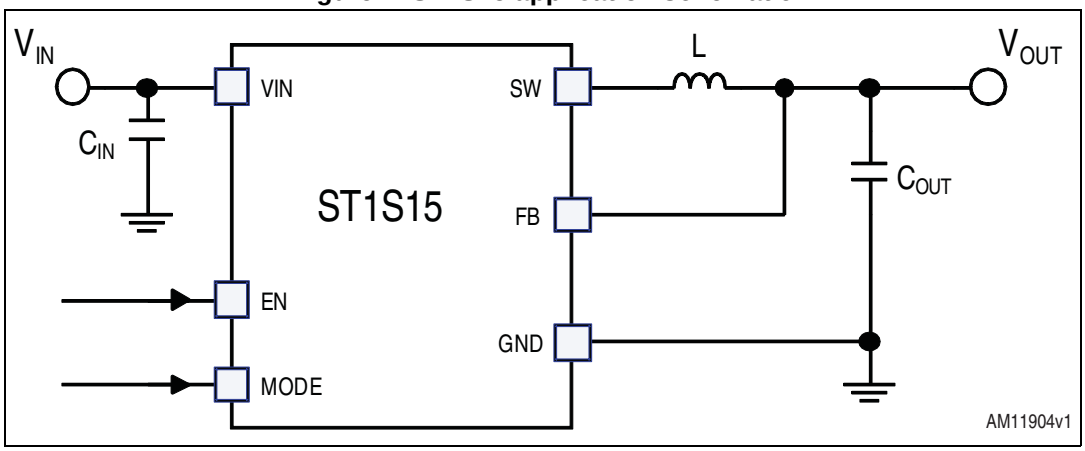


Table 2. Typical external components

Component	Manufacturer	Part number	Value	Size
C_{IN}	Murata	GRM155R60J475ME87	4.7 µF	0402
C_{OUT}	Murata	GRM155R60G475ME87 (1)	4.7 µF	0402
		GRM155R60J475ME87		
L	Murata	LQM21PNR47MC0D	470 nH	2.0 x 1.25 x 0.5 mm

1. For $V_{OUT} \leq 1.82$ V.

Note: All the above components refer to a typical application. Operation of the ST1S15 is not limited to the choice of these external components.

2 Pin configuration

Figure 2. Pin connections (top view)

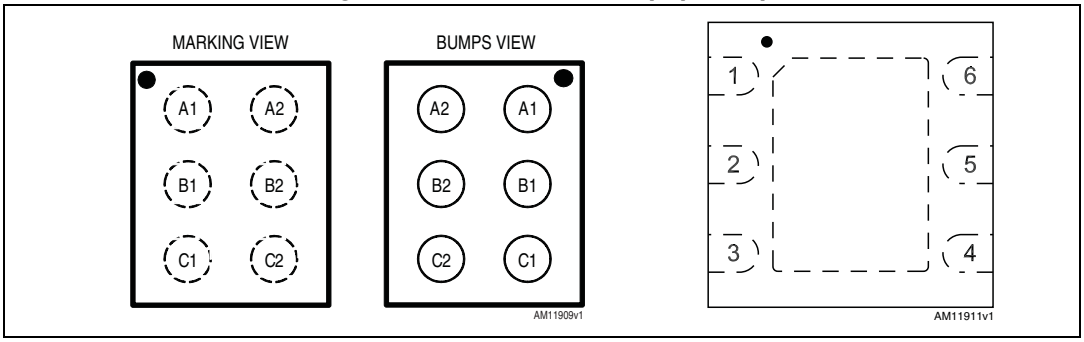


Table 3. Pin description

Pin name	Flip Chip	DFN6	Description
V_{IN}	A2	1	High-side switch connection and IC supply.
EN	B2	2	ENABLE pin with positive logic. The IC goes into shutdown if pulled low. Do not leave this pin floating.
GND	C2	3	Power and IC supply ground.
FB	C1	4	Feedback input.
SW	B1	5	Inductor connection to internal PFET and NFET.
MODE	A1	6	Operation mode selection: - LOW => Automatic operation PFM or PWM according to output load; - HIGH => Forced PWM operation. Do not leave this pin floating.
Epad	-	Epad	Exposed pad to be connected to ground

3 Maximum ratings

Table 4. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{IN}	Power and signal supply voltage	- 0.3 to + 6.0	V
EN, MODE	Logic input pins	- 0.3 to + 6.0	V
FB, SW	Feedback and switching pins	-0.3 to V_{IN} + 0.3	V
T_{AMB}	Operating ambient temperature	- 40 to 85	°C
T_J	Junction temperature	- 40 to 150	°C
T_{STG}	Storage temperature	- 65 to 150	°C

Note: Absolute maximum ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

Table 5. Thermal data

Symbol	Parameter	DFN6	Flip Chip	Unit
R_{thJA}	Thermal resistance junction-ambient	80	130	°C/W

Table 6. ESD performance

Symbol	Parameter	Value	Unit
ESD	Human body model	± 2000	V
	Machine model	± 100	

4 Electrical characteristics

- 40 °C < T_A < 85 °C, C_{IN} = 4.7 µF nominal, C_{OUT} = 4.7 µF nominal, L = 470 nH, typical values are at T_A = 25 °C, V_{EN} = V_{IN} unless otherwise specified.

Table 7. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
General section						
V_{IN}	Operating input voltage range		2.3		5.5	V
V_{UVLO}	Undervoltage lockout threshold	V_{IN} rising		2.1	2.2	V
		V_{IN} falling	1.8	1.9		
I_Q	PFM mode quiescent current	No load		45	60	µA
	PWM mode quiescent current	No load		15		mA
	Shutdown current	V_{EN} = 0		0.5	5	µA
f_{SW}	Switching frequency		5.4	6	6.6	MHz
I_{OUT}	Continuous output current (1)	$V_{IN} \geq V_{OUT}$ + 0.40 V	500			mA
I_{SC}	Short-circuit current (2)				1200	mA
$I_{PFM-PWM}$	PFM to PWM transition	V_{IN} = 3.6V, V_{OUT} = 1.82 V		200		mA
	PWM to PFM transition			100		
h	Efficiency (V_{IN} = 3.6 V, V_{OUT} = 1.82 V)	I_{OUT} = 10 mA PFM mode		80		%
		I_{OUT} = 150 mA		83		
t_{ON}	Startup time	V_{EN} from low to high, V_{IN} = 3.6 V, V_{OUT} = 1.82 V		260		µs
T_{SHDN}	Thermal shutdown			125		°C
	Hysteresis			30		°C
Output voltage						
V_{OUT}	Accuracy (ST1S15x18)	2.3 ≤ V_{IN} ≤ 5.5 V, I_{OUT}= 10 mA, PWM mode, -40 ≤ T_A ≤ 85 °C	1.78	1.82	1.86	V
		2.3 ≤ V_{IN} ≤ 5.5 V, I_{OUT}= 10 mA, PFM mode, -40 ≤ T_A ≤ 85 °C	1.78	1.82	1.86	
	Load regulation	2.3 ≤ V_{IN} ≤ 5.5 V, V_{OUT}=1.82 V, I_{OUT} = 0 to 500 mA, PWM mode, -40 ≤ T_A ≤ 85 °C		-1.5		%
	Accuracy (ST1S15x28)	3.2 ≤ V_{IN} ≤ 5.5 V, I_{OUT}= 10 mA, PWM mode, -40 ≤ T_A ≤ 85 °C	2.74	2.8	2.86	V
		3.2 ≤ V_{IN} ≤ 5.5 V, I_{OUT}= 10 mA, PFM mode, -40 ≤ T_A ≤ 85 °C	2.74	2.8	2.86	
	Load regulation	3.2 ≤ V_{IN} ≤ 5.5 V, V_{OUT} = 2.8 V, I_{OUT} = 0 to 500 mA, PWM mode, - 40 ≤ T_A ≤ 85 °C		-1.5		%

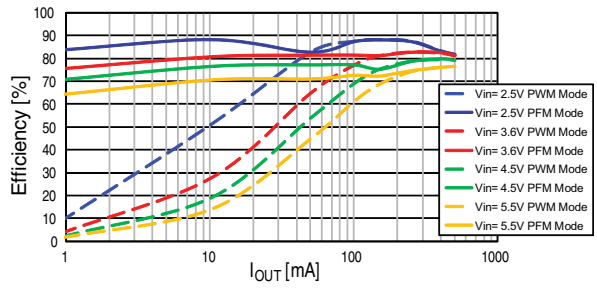
Table 7. Electrical characteristics (continued)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{OUT_Ripple}	Peak-to-Peak output voltage ripple	PWM mode, I_{OUT} = 150 mA, V_{IN} = 3.6 V, V_{OUT} = 1.82 V		10		mV
		PFM mode, I_{OUT} = 150 mA, V_{IN} = 3.6 V, V_{OUT} = 1.82 V		30		mV
I_{LKFB}	FB pin leakage current	V_{FB} = 5.5 V			9	µA
V_{IN_TR}	Line transient response. Output voltage variation over nominal DC level. $t_R = t_F$ = 10 µs Case 1: V_{IN} = 2.5 to 3.1 V Case 2: V_{IN} = 3.9 to 4.5 V	I_{OUT} = 50 mA, V_{OUT} = 1.82 V		±50		mV
		I_{OUT} = 250 mA, V_{OUT} = 1.82 V				
I_{OUT_TR}	Load transient response t_R=t_F=0.1µs. Case 1: V_{IN}=2.5 V Case 2: V_{IN}=3.6 V Case 3: V_{IN}=4.5 V	I_{OUT} = 0 to 150 mA, V_{OUT} = 1.82 V		±50		mV
		I_{OUT} = 50 to 250 mA, V_{OUT} = 1.82 V		±70		
		I_{OUT} = 150 to 400 mA, V_{OUT} = 1.82 V		±70		
Logic Inputs						
V_{IL}	Low-level input voltage (EN, MODE pins)				0.4	V
V_{IH}	High-level input voltage (EN, MODE pins)		1.2			V
I_{LK-I}	Input leakage current (EN, MODE pins)	V_{EN} = V_{MODE} = 5.5 V		0.01	1	µA
Power Switches						
R_{DSON}	P-channel MOSFET on-resistance			300	400	mΩ
	N-channel MOSFET on-resistance			350	450	
I_{LPEAK}	P-channel peak current limit	Over input voltage range	900	1000	1200	mA
I_{LKG-P}	P-channel leakage current	V_{IN} = 5.5 V, V_{EN}= 0			1	µA
I_{LKG-N}	N-channel leakage current	V_{SW} = 5.5 V, V_{EN}= 0			1	µA

1. Not tested in production. This value is guaranteed by correlation with R_{DSON}, peak current limit and operating input voltage.
2. Not tested in production. This parameter is guaranteed by peak current limit.

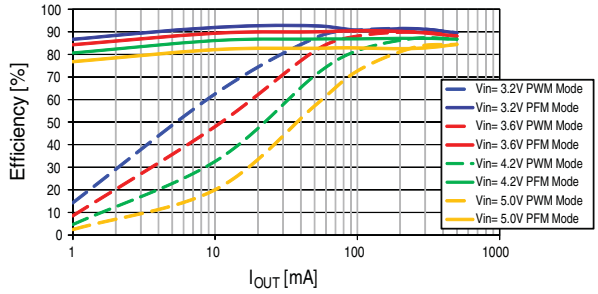
5 Typical performance characteristics

Figure 3. Efficiency vs. output current (V_{OUT} = 1.82 V)



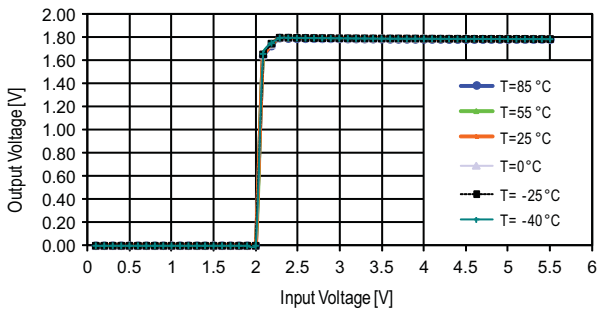
V_{EN} = V_{IN}, I_{OUT} = 1 mA to 500 mA

Figure 4. Efficiency vs. output current (V_{OUT} = 2.8 V)



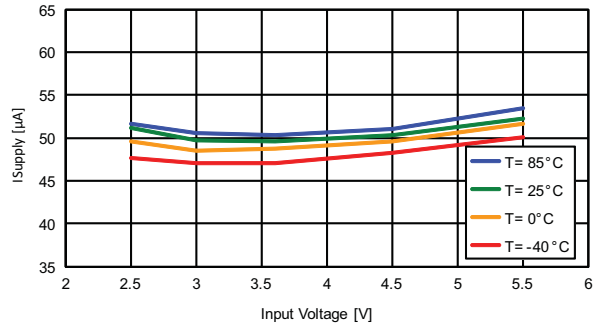
V_{EN} = V_{IN}, I_{OUT} = 1 mA to 500 mA

Figure 5. Output voltage vs. input voltage



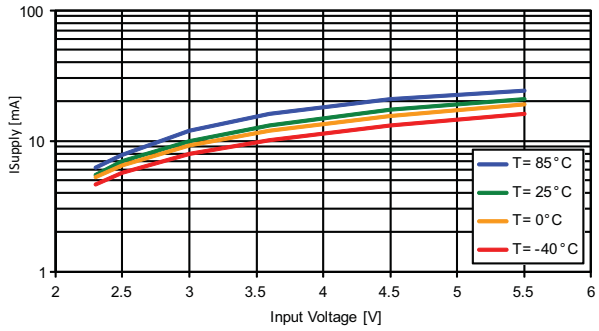
V_{IN} = 0 to 5.5 V (step 0.1 V), I_{OUT} = 500 mA, Mode = GND, V_{EN} = V_{IN}

Figure 6. Supply current vs. input voltage in auto mode



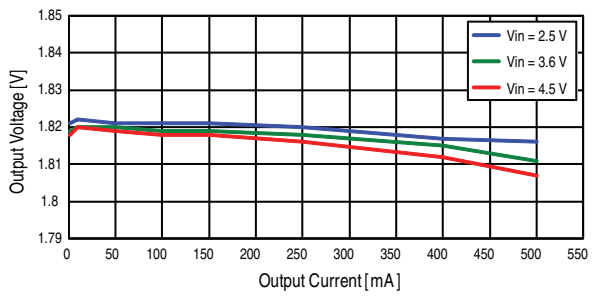
V_{IN} = 2.5 V to 5.5 V, Mode = GND, V_{OUT} = 1.82 V, V_{EN} = V_{IN}

Figure 7. Supply current vs. input voltage in PWM mode



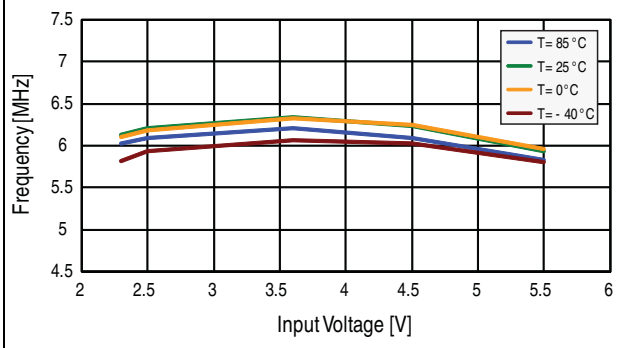
V_{IN} = 2.3 V to 5.5 V, Mode = V_{IN}, V_{OUT} = 1.82 V, V_{EN} = V_{IN}

Figure 8. Output voltage vs. output current



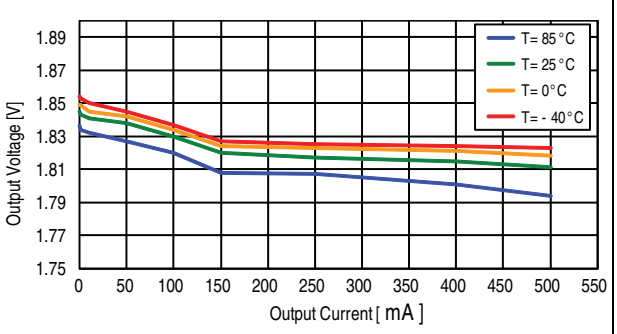
V_{EN} = V_{IN}, Mode = V_{IN}, V_{OUT} = 1.82 V

Figure 9. Frequency vs. input voltage



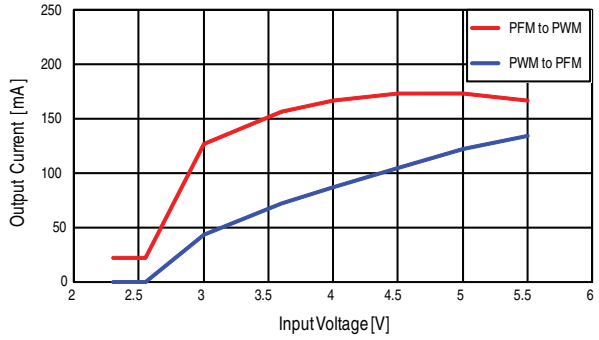
V_{IN} = 2.3 V to 5.5 V, I_{OUT} = 10 mA, Mode = V_{IN}, V_{EN} = V_{IN}

Figure 10. Output voltage vs. output current



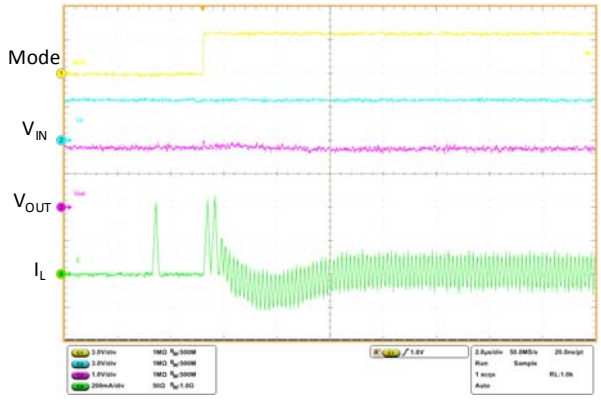
V_{IN} = 3.6 V, I_{OUT} = 0 to 500 mA, Mode = GND, V_{EN} = V_{IN}

Figure 11. Mode transition vs. input voltage



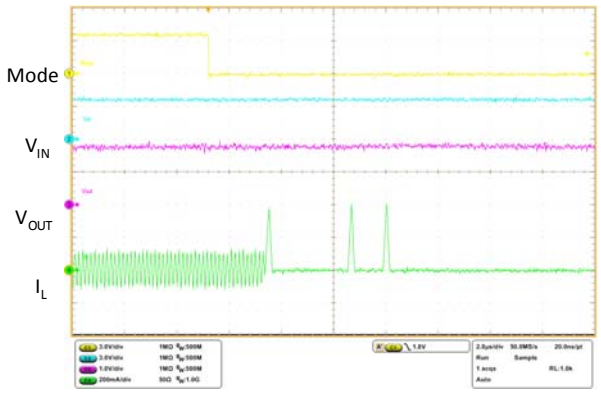
V_{IN} = Enable, V_{OUT} = 1.82 V, Mode = GND

Figure 12. Mode transition PFM to PWM



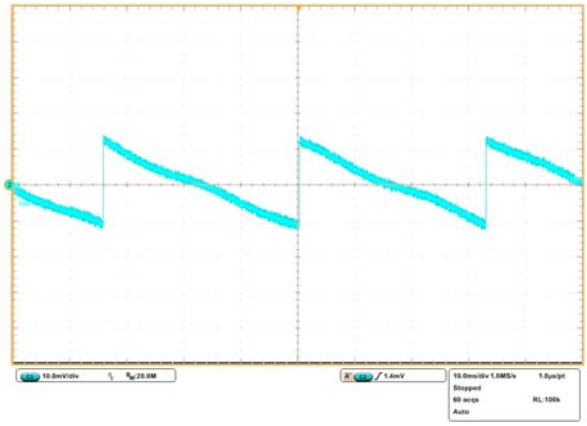
V_{IN} = 3.6 V, V_{OUT} = 1.82 V, Mode = 0 to 3.6 V, Load = 180 Ω

Figure 13. Mode transition PWM to PFM



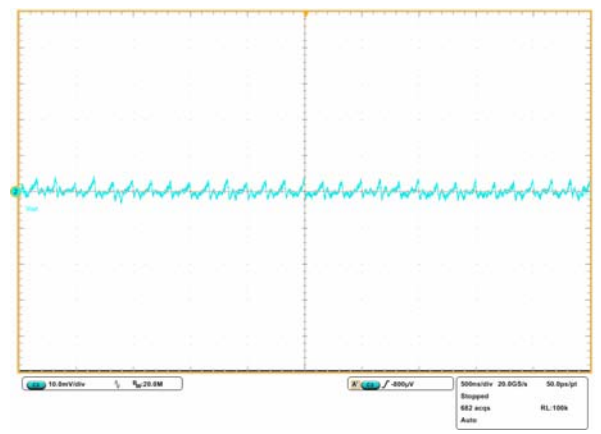
V_{IN} = 3.6 V, V_{OUT} = 1.82 V, Mode = 3.6 to 0 V, Load = 180 Ω

Figure 14. Output voltage ripple



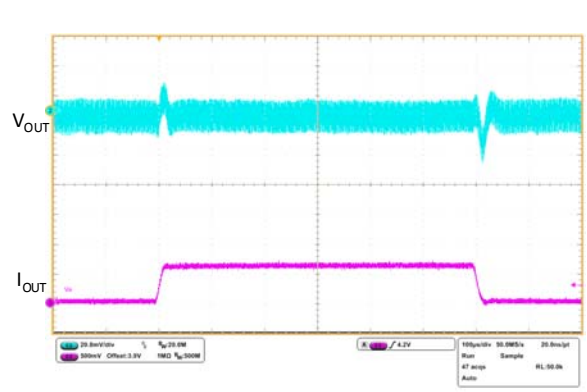
V_{IN} = 3.6 V, V_{OUT} = 1.82 V, Mode = GND, V_{EN} = $V_{IN,}$ No load

Figure 15. Output voltage ripple



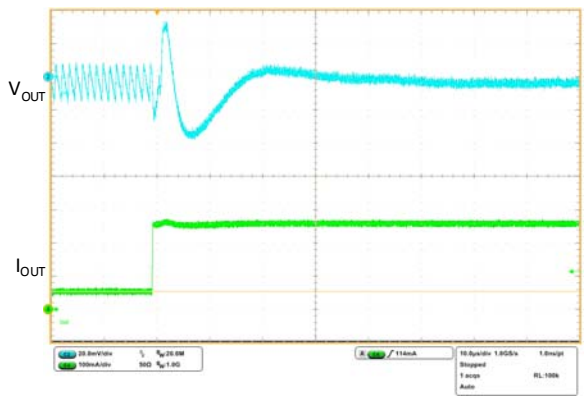
V_{IN} = 3.6 V, V_{OUT} = 1.82 V, I_{OUT} = 500 mA, V_{EN} = V_{IN}

Figure 16. Line transient



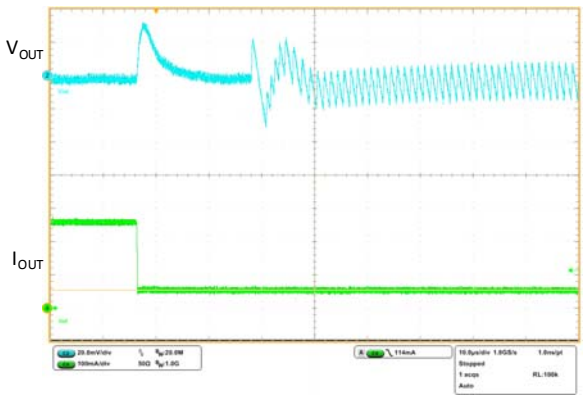
V_{IN} = 3.9 to 4.5 V, t_r = t_f = 10 µs, I_{OUT} = 50 mA, V_{EN} = V_{IN}

Figure 17. Load transient I_{OUT} = 50 to 250 mA



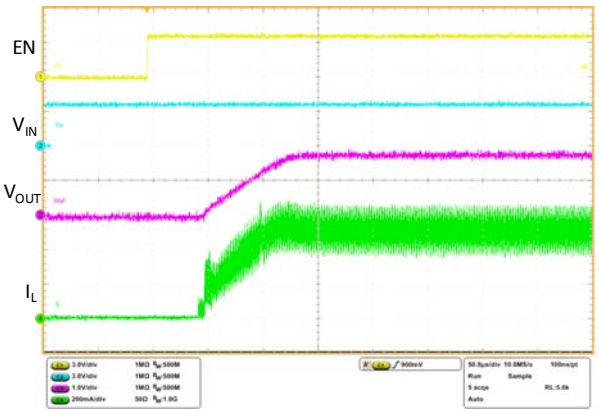
V_{IN} = 3.6 V, t_r = 100 ns, I_{OUT} = 50 mA to 250 mA, V_{EN} = V_{IN}, Mode = GND

Figure 18. Load transient I_{OUT} = 250 to 50 mA



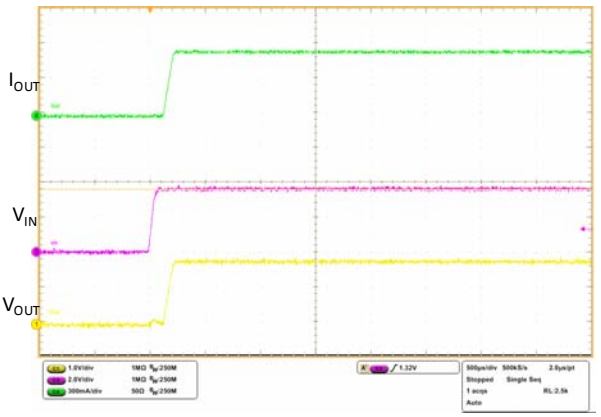
V_{IN} = 3.6 V, t_f = 100 ns, I_{OUT} = 250 mA to 50 mA, V_{EN} = V_{IN}, Mode = GND

Figure 19. Enable startup



V_{IN} = 3.6 V, Enable = 0 to 3.6 V, Mode = V_{IN}, V_{OUT} = 1.82 V, Load = 3.6 Ω

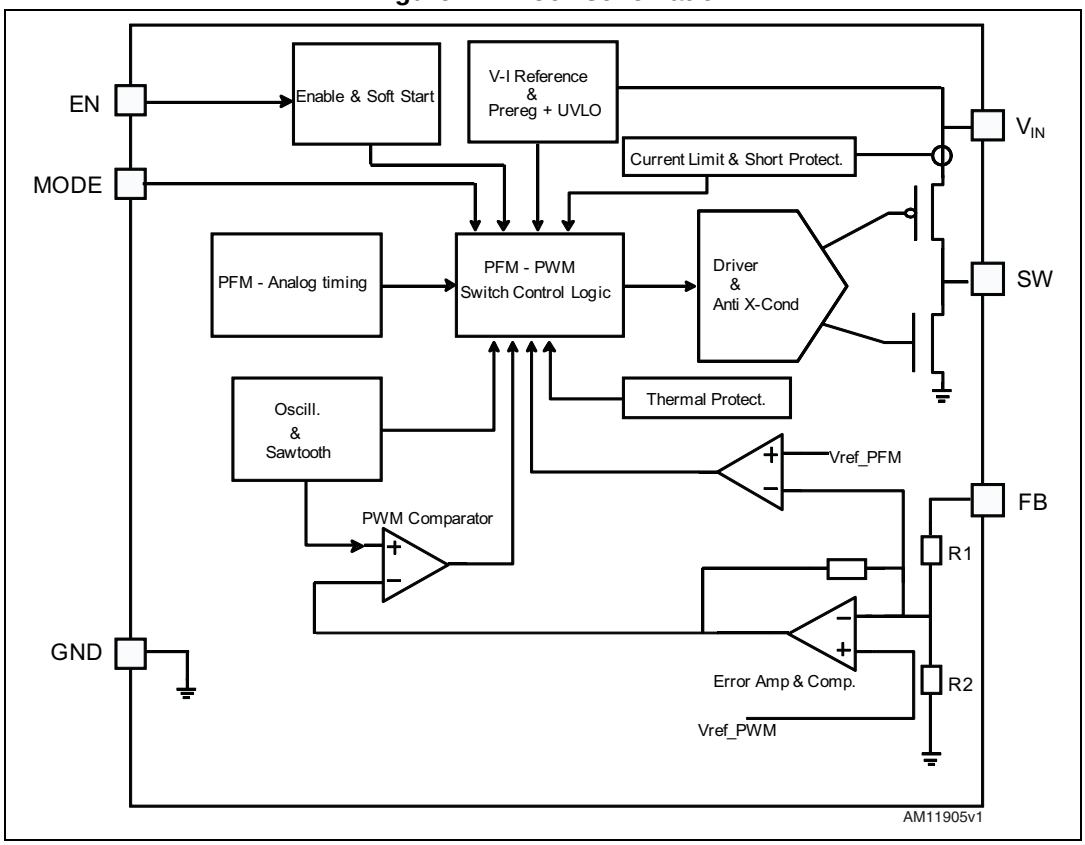
Figure 20. V_{IN} startup



V_{IN} = 0 to 2.5 V, Enable = V_{IN}, Mode = GND, V_{OUT} = 1.82 V, Load = 3.3 Ω

6 Block schematic

Figure 21. Block schematic



7 Detailed description

7.1 General description

The ST1S15 is a fixed voltage mode PWM step-down DC-DC converter which operates with typically 6 MHz fixed frequency pulse width modulation (PWM) at moderate to heavy load currents. At light load currents the converter can automatically enter PFM (pulse frequency mode) mode.

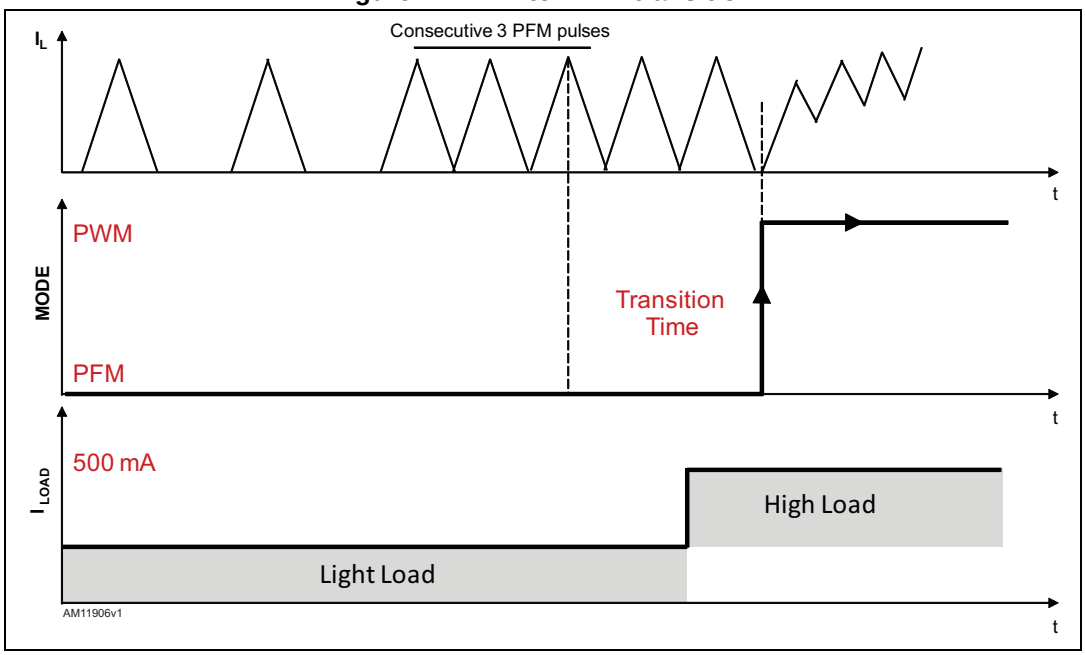
To make the device work, few components are required: an inductor and two capacitors. It has been designed to work properly with X5R or X7R SMD ceramic capacitors both at the input and at the output. These kinds of capacitors, thanks to their very low series resistance (ESR), minimize the output voltage ripple. In addition, the chosen inductor must be able to not saturate at the peak current level.

7.2 Mode transition

The ST1S15 can work in PWM mode or in PFM mode according to the different operating conditions. If the MODE pin is pulled high, the device works only in PWM mode even at light or no load. If the MODE pin is low, the operation changes according to the average input current handled by the device. At low output current the device works in PFM mode in order to obtain very low power consumption and very good efficiency. When the output current increases, the device automatically switches to PWM mode in order to deliver the power needed by the load.

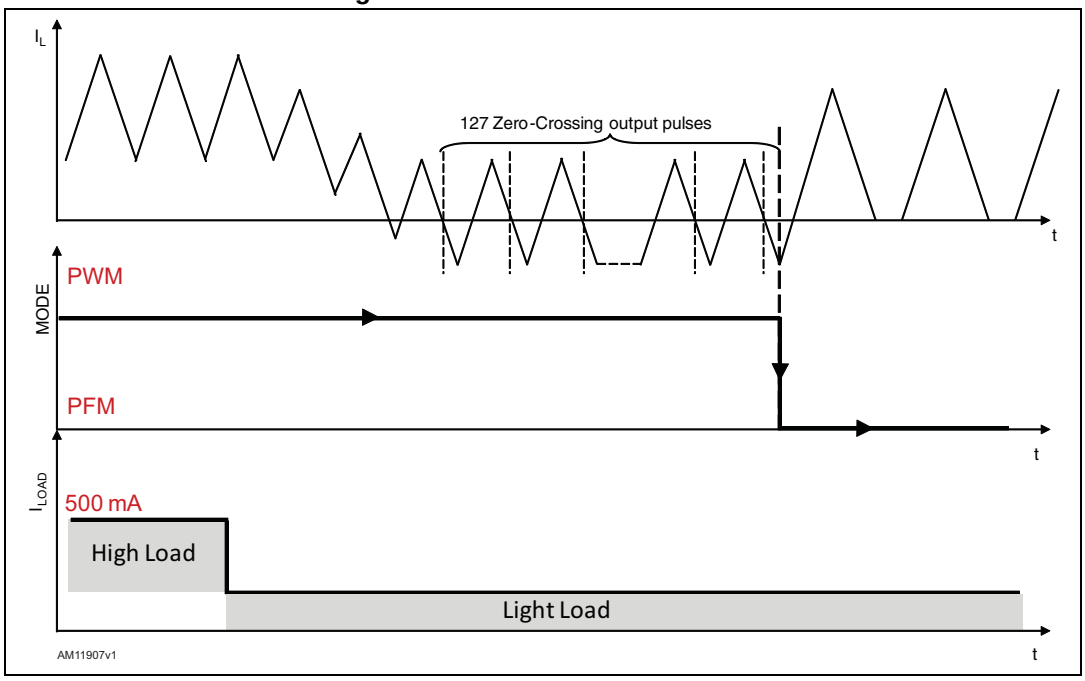
The ST1S15 passes from PFM to PWM when 3 consecutive PFM pulses occur. This means that the PFM has reached its maximum current capability and the device needs to go into PWM mode. The whole PWM circuitry starts after a transition time. During this time the duration of the PFM pulses are increased to about 350 ns so as to provide higher current capability. After startup of the PWM circuitry, the ST1S15 switches to PWM operation.

Figure 22. PFM to PWM transition



The transition from PWM to PFM mode occurs when the load current decreases and the coil current becomes negative. After the zero-crossing output goes up for 127 consecutive times the device switches to PFM mode.

Figure 23. PWM to PFM transition



7.3 Soft-start

The internal soft-start is enabled after V_{IN} reaches the UVLO threshold and the EN pin is high or for startup after enable. An overtemperature shutdown event or over short-circuit event also activates the soft-start sequence.

It eliminates the in-rush current problem during the startup phase. During the soft-start the device works always in PWM regardless of the status of the Mode pin.

7.4 Short-circuit protection

The short-circuit protection begins when there is a short between the device output and ground. In this case the output voltage value is lower than the voltage reference and the overcurrent protection comparator output is high. When this happens the power stage (Pch and Nch) turns off and a soft-start phase starts. The device repeats the soft-start sequence during the short-circuit condition.

7.5 Undervoltage lockout (UVLO)

The UVLO circuit prevents the device from malfunctioning when the input voltage is not high enough. The device is in shutdown mode, when the input voltage is below the UVLO threshold. The hysteresis of 200 mV prevents unstable operation when the input voltage is close to the UVLO threshold.

7.6 Thermal protection

The device also has thermal shutdown protection, which is active when the junction temperature reaches 125 °C. In this case both the high and low-side MOSFETs are turned off.
Once the junction temperature goes back below 95 °C, the device resumes normal operation.

7.7 Overcurrent protection

The overcurrent protection is used to limit the maximum inductor current. This current flowing through the Pch of the power stage causes a voltage drop, across its RDSON, at the switching node. A comparator compares the switching node voltage with a reference voltage VR. To generate the VR voltage a current generator is used, which causes a drop across a Pch of the same kind as the power stage. When the switching node voltage is lower than VR, the comparator output goes high and the power Pch turns off.

7.8 Enable function

The ST1S15 features an enable function (pin 2 or B2). When the EN voltage is higher than 1.2 V the device is ON, and if it is lower than 0.4 V the device is OFF. In shutdown mode the consumption is lower than 5 µA.
The EN pin does not have an internal pull-up, which means that the EN pin cannot be left floating.

If the enable function is not used, the EN pin must be connected to V_{IN}.

8 Application Information

8.1 Input and output capacitor

It is recommended to use ceramic capacitors with X5R or X7R dielectric and low ESR. The input capacitor is used to filter any disturbance present in the input line and to obtain stable operation. The output capacitor is very important to satisfy the output voltage ripple requirement.

The output voltage ripple (V_{OUT_RIPPLE}), in continuous mode, must be calculated:

Equation 1

$$V_{OUT\_RIPPLE} = \Delta I_L \times \left[ESR + \frac{1}{8 \times C_{OUT} \times f_{SW}} \right] + \frac{V_{IN} \times ESL}{L}$$

where ΔI_L is the ripple current and f_{SW} is the switching frequency.

The use of ceramic capacitors with voltage ratings in the range higher than 1.5 times the maximum input or output voltage is recommended.

8.2 Inductor

The inductor is the key passive component for switching converters. The internal compensation is optimized to operate with an output filter of L = 0.47 µH and C_{OUT} = 4.7 µF.

In addition to the inductance value, in order to avoid saturation, the maximum saturation current of the inductor must be higher than that of the I_{PEAK}.

The peak current of the inductor must be calculated as:

Equation 2

$$I_{PEAK} = I_{OUT} + \frac{V_{OUT} \times (V_{IN\_MAX} - V_{OUT})}{2 \times V_{IN\_MAX} \times f_{SW} \times L}$$

The following inductor p/ns from different suppliers have been tested in the ST1S15 converters.

Table 8. Inductors

Manufacturers	p/ns	Dimensions (in mm)
Murata	LQM21PNR47MC0D	2.0 x 1.25 x 0.5
	LQM21PNR54MG0D	2.0 x 1.25 x 0.5
	LQH32PNR47NN0L	3.2 x 2.7 x 1.55
TDK	MLP2012SR47T	2.0 x 1.25 x 0.5
	VLS2010ET-1R0N	2.0 x 2.0 x 1.0

8.3 Layout guidelines

Due to the high switching frequency and peak current, the layout is an important design step for all switching power supplies. If the layout is not done carefully, important parameters such as stability, efficiency, line and load regulation and output voltage ripple may be compromised.

Short, wide traces must be implemented for main current and for power ground paths. The input capacitor must be placed as close as possible to the device pin as well as the inductor and output capacitor.

The FEEDBACK pin (FB) is a high impedance node, so the interference can be minimized by placing the routing of the feedback node as far as possible from the high current paths.

A common ground node minimizes ground noise.

The exposed pad of the DFN package must be connected to the common ground node.

Figure 24. DFN layout recommended (not to scale)

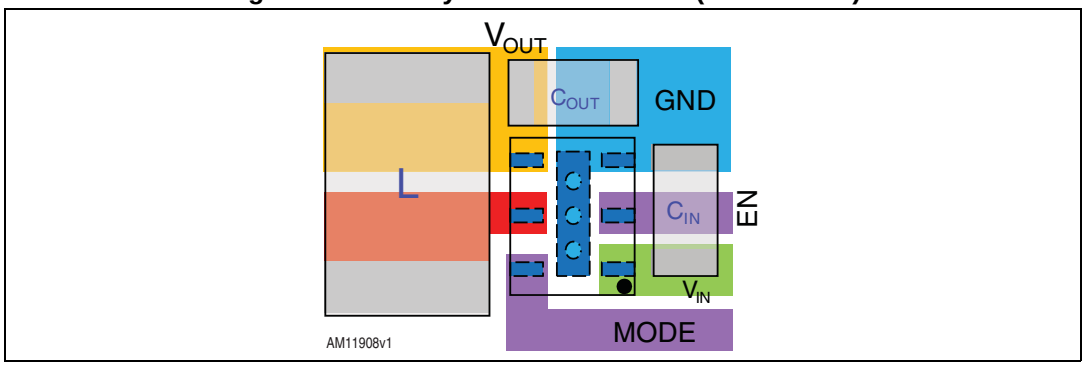
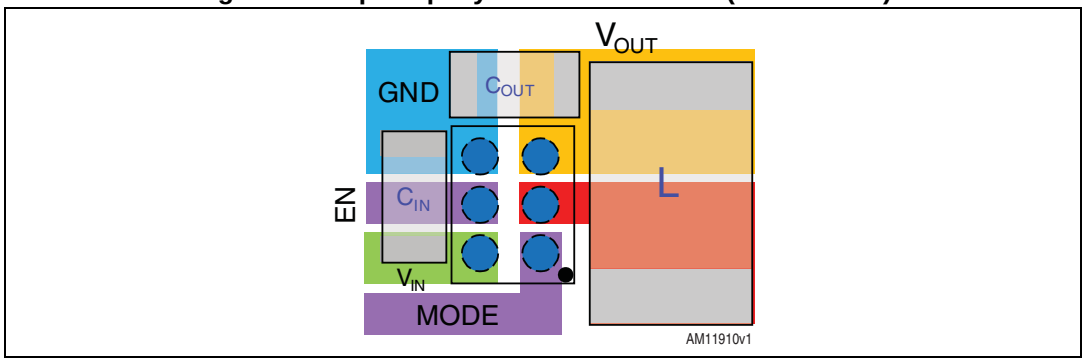


Figure 25. Flip-Chip layout recommended (not to scale)



9 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK is an ST trademark.

Table 9. DFN6 (2 x 2 mm) mechanical data

Dim.	(mm)		
	Min.	Typ.	Max.
A	0.51	0.55	0.60
A1	0	0.02	0.05
b	0.18	0.25	0.30
D		2.00	
D2	1.30	1.45	1.55
E		2.00	
E2	0.85	1.00	1.10
e		0.50	
L	0.15	0.25	0.35

Figure 26. DFN6 (2 x 2 mm) package dimensions

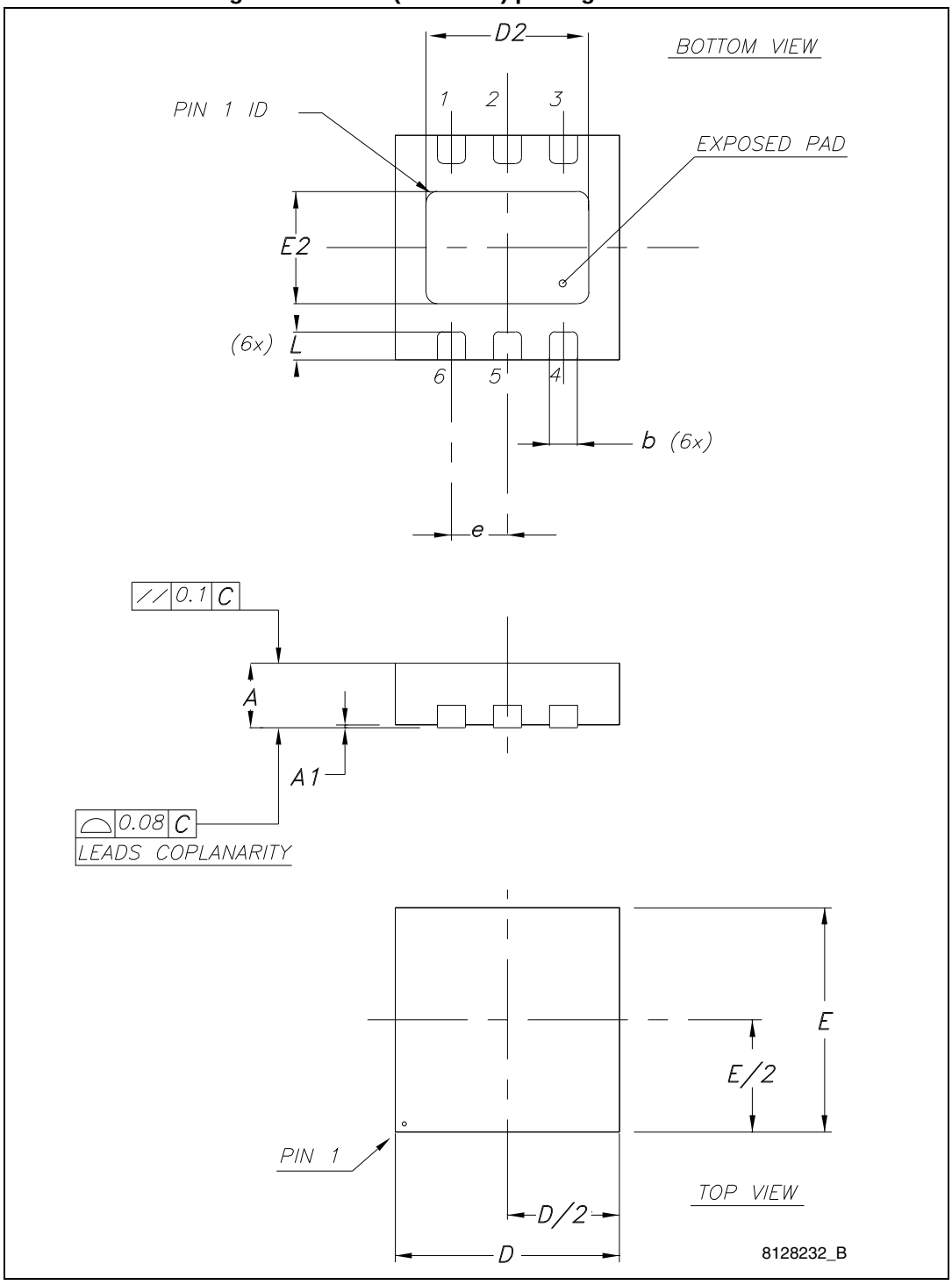


Figure 27. DFN6 footprint recommended data (dimensions in mm)

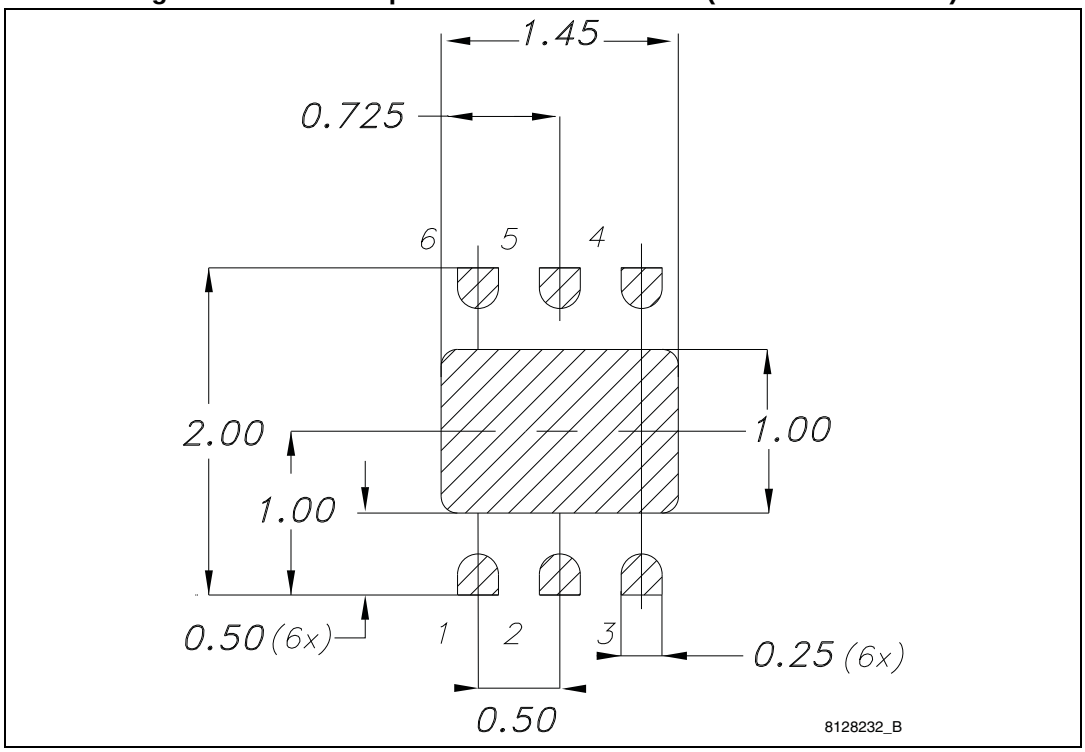


Table 10. Flip Chip 6 mechanical data

Dim.	(mm)		
	Min.	Typ.	Max.
A	0.52	0.56	0.6
A1	0.17	0.20	0.23
A2	0.35	0.36	0.37
b	0.23	0.25	0.29
D	1.16	1.19	1.22
D1		0.8	
e		0.4	
E	0.905	0.935	0.965
E1		0.4	
f_D		0.272	
f_E		0.200	
ccc		0.075	

Figure 28. Flip Chip 6 package dimensions

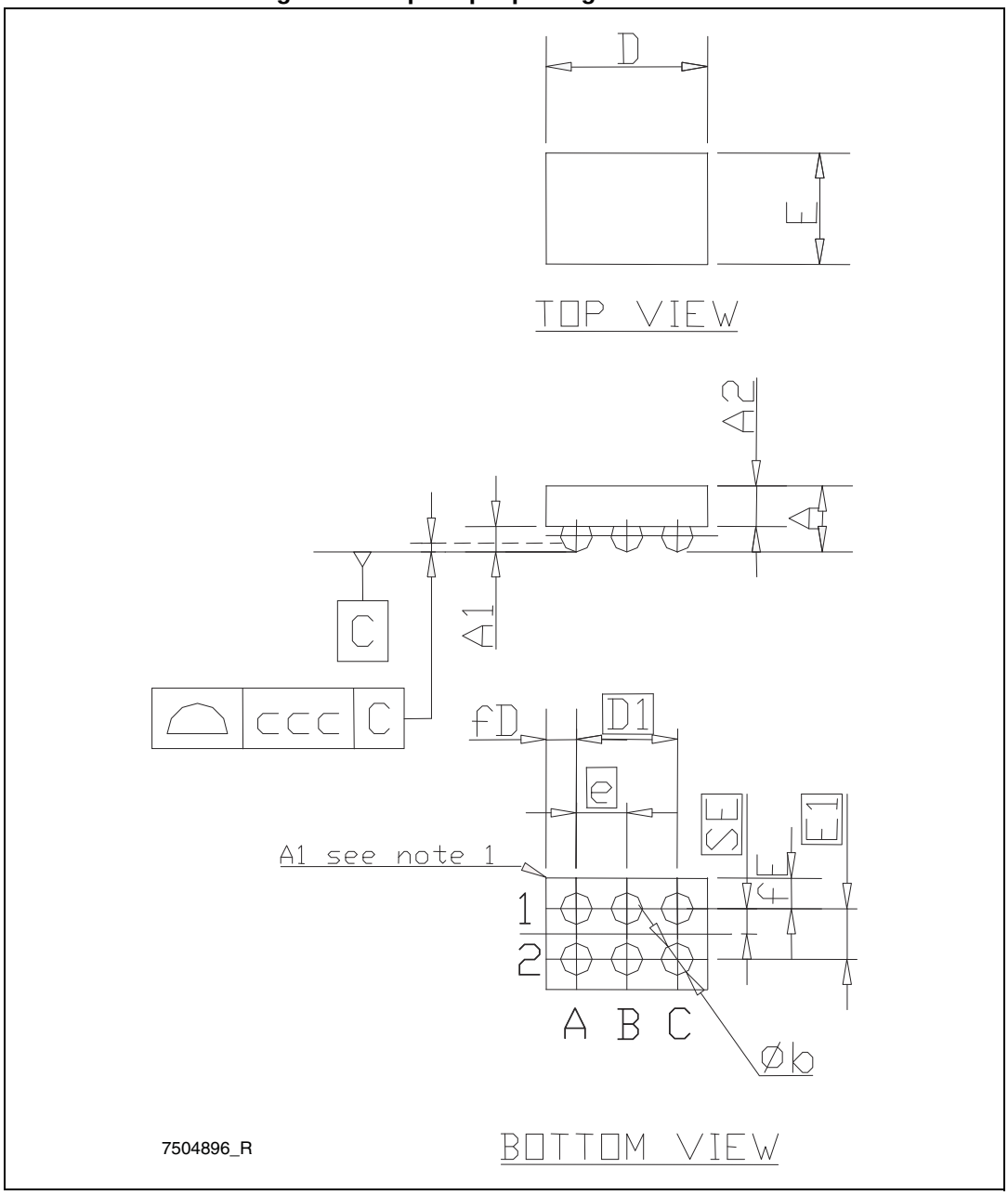
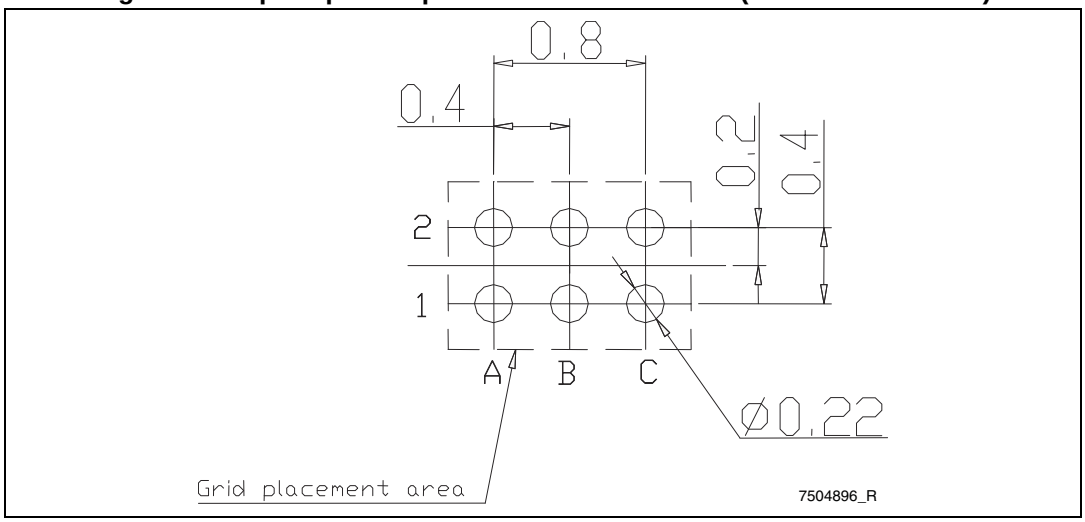
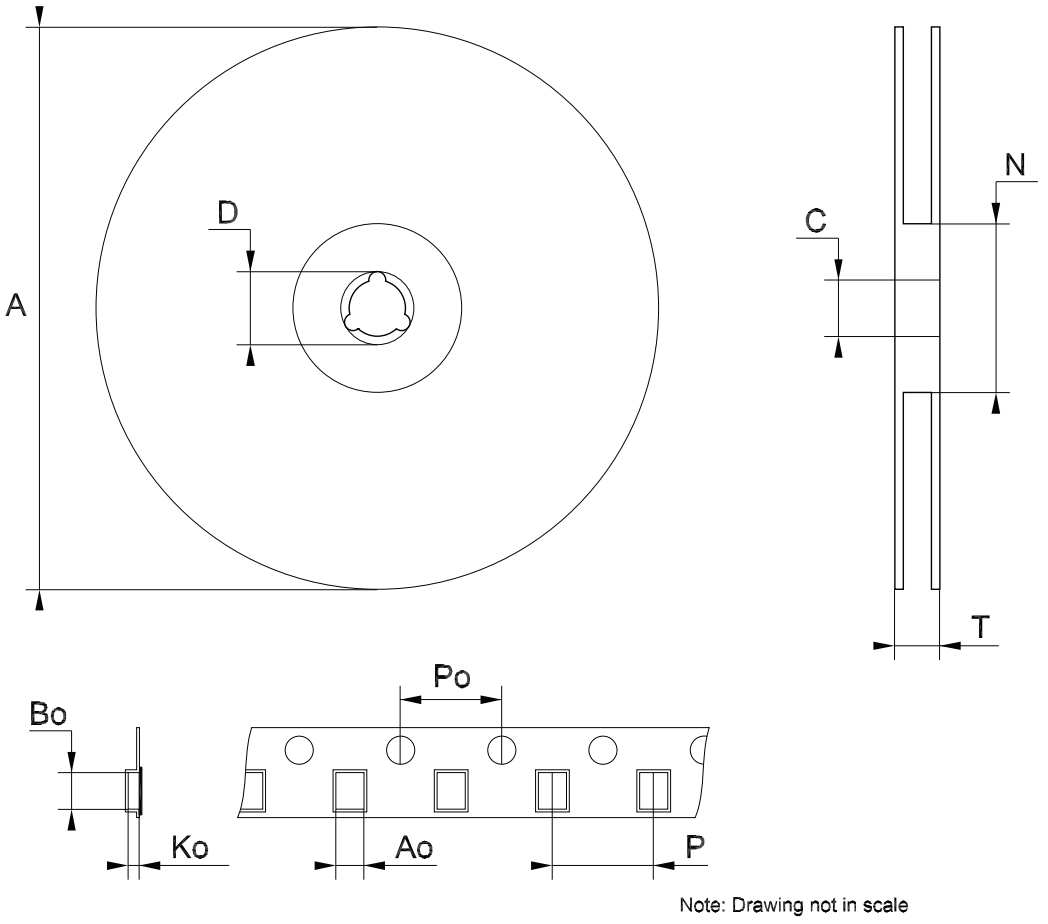


Figure 29. Flip Chip 6 footprint recommended data (dimensions in mm)



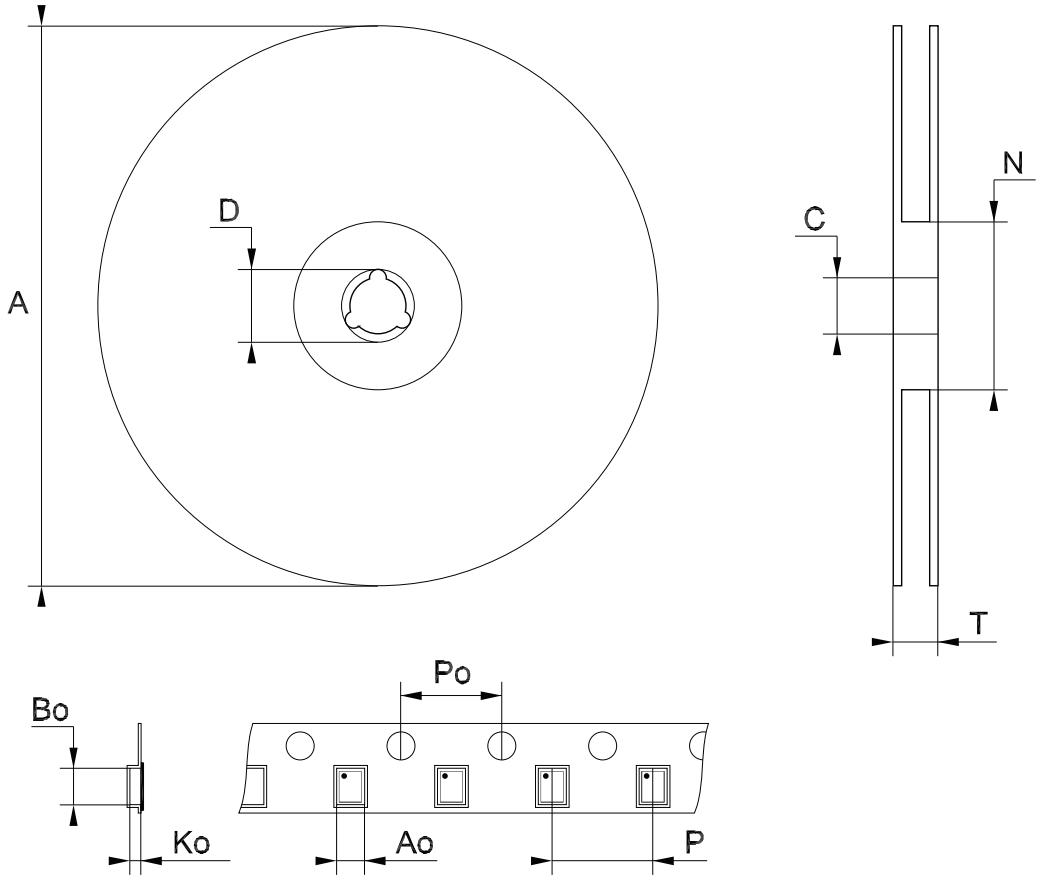
Tape & reel QFNxx/DFNxx (2x2 mm) mechanical data

Dim.	mm.			inch.		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			180			7.087
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			14.4			0.567
Ao	2.1	2.2	2.3	0.083	0.087	0.091
Bo	2.1	2.2	2.3	0.083	0.087	0.091
Ko	0.65	0.75	0.85	0.026	0.030	0.033
Po		4			0.157	
P		4			0.157	



Tape & reel Flip-Chip 6 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A			180
C	12.8		13.2
D	20.2		
N	60		
T			14.4
Ao	1.01	1.06	1.11
Bo	1.26	1.31	1.36
Ko	0.61	0.66	0.71
Po	3.9		4.1
P	3.9		4.1



Note: Drawing not in scale

10 Different output voltage versions of the ST1S15 available on request

Options available on request:

- 0.8 V
- 1 V
- 1.05 V
- 1.2 V
- 1.25 V
- 1.5 V
- 1.8 V
- 1.85 V
- 1.875 V
- 2.5 V
- 3 V
- 3.3 V

11 Revision history

Table 11. Document revision history

Date	Revision	Changes
07-Jun-2012	1	First release.
04-Mar-2013	2	Modified: D1 and E1 values *Table 10 on page 21*.
27-Aug-2013	3	Updated *Table 1: Device summary on page 1*, *Table 7: Electrical characteristics on page 6*, *Section 9: Package mechanical data* and *Section 10: Different output voltage versions of the ST1S15 available on request*. Minor text changes.

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